



Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	6Ω @ V _{GS} = 5V	200mA

N-CHANNEL ENHANCEMENT MODE MOSFET

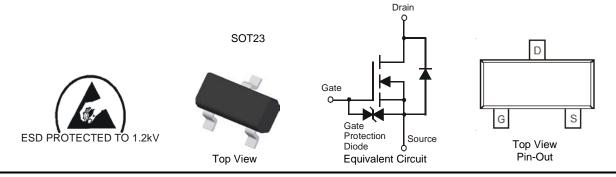
Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The 2N7002AQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Alloy 42 Lead-Frame. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002AQ-7	SOT23	3,000/Tape & Reel
2N7002AQ-13	SOT23	10,000/Tape & Reel

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:

	SOT23					MN1 = Product Type Marking Code						
			MN1	ΜY		YN Y c	I = Produc I = Date Co or Ÿ = Year = Month (e:	de Markin (ex: H = 20	g)20)			
Date Code Key							X	·	,			
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	
Code	С		Н		J	K	L	М	Ν	0	Р	
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Т
Code	1	2	3	4	5	6	7	8	9	0	Ν	1

2029 R **Dec**

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Power Management Functions



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$	ID	180 130 115	mA
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$ $T_A = +100^{\circ}C$	ID	220 160 140	mA
Maximum Continuous Body Diode Forward Curren	nt (Note 6)		ls	220	mA
Pulsed Drain Current (10µs pulse, duty cycle = 1%	6)	I _{DM}	800	mA	

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Total Power Dissipation	(Note 5)	D-	370	mW	
	(Note 6)	PD	540	11177	
Thermal Desistance, lunction to Ambient	(Note 5)	6	348		
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _{0JC}	91		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)		<u> </u>					
Drain-Source Breakdown Voltage			60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ $T_C = +25^{\circ}C$ @ $T_C = +125^{\circ}C$		I _{DSS}	_	_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(th)}	1.2		2.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance @ T ₁ = ±25°C		Р		3.5	6	Ω	$V_{GS} = 5.0V, I_D = 0.115A$
	@ T _J = +125°C	R _{DS(ON)}	_	3.0	5	12	$V_{GS} = 10V, I_D = 0.115A$
Forward Transconductance		g fs	80	_	_	mS	$V_{DS} = 10V, I_D = 0.115A$
DYNAMIC CHARACTERISTICS (Note	8)						
Input Capacitance			_	23	—	pF	
Output Capacitance		Coss	_	3.4	—	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		Crss	_	1.4	—	pF	
Gate Resistance			_	260	400	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (No	ote 8)						
Turn-On Delay Time			_	10	_	ns	V _{DD} = 30V, I _D = 0.115A, R _L = 150
Turn-Off Delay Time		t _{D(OFF)}		33	_	ns	Ω , V _{GEN} = 10V, R _{GEN} = 25 Ω

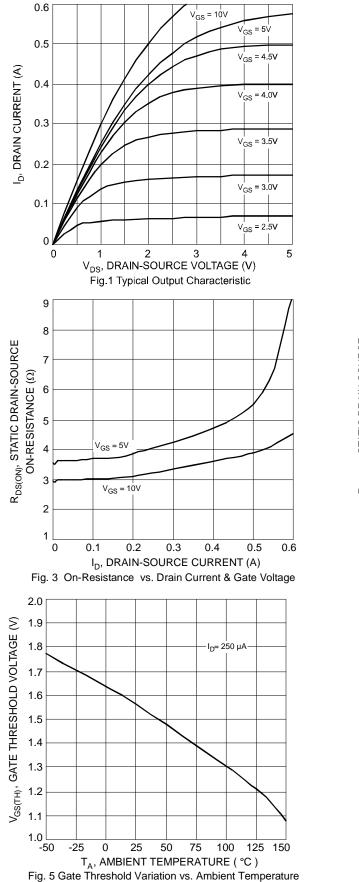
Notes:

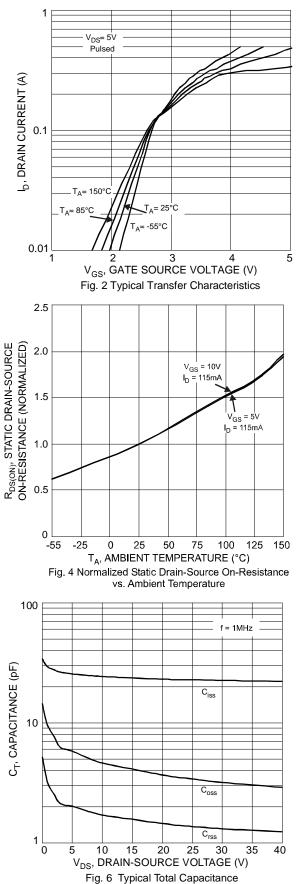
Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

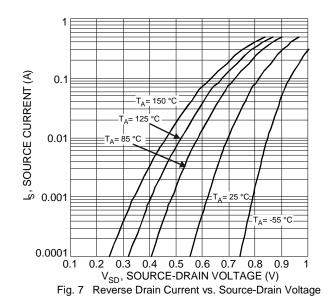


2N7002AQ



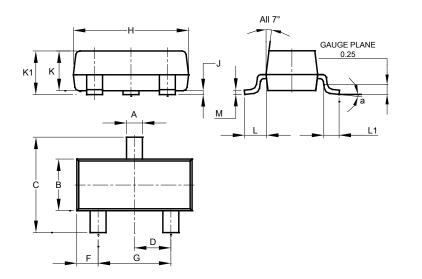






Package Outline Dimensions

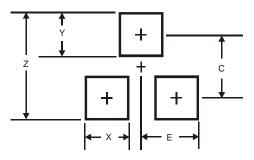
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SO	T23	
Dim	Min	Max	Тур
Α	0.37	0.51	0.40
В	1.20	1.40	1.30
c	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
К	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
М	0.085	0.150	0.110
а		8°	
All	Dimens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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